



## Other Specifications

Platen Maximum Temperature: 300°C

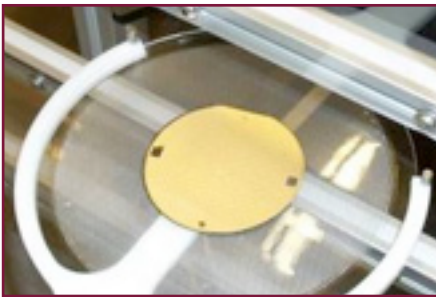
Substrate Sizes (round): 2 in, 3 in, 100 mm, 125 mm, 150 mm, 200 mm

Constant Force Mode: 0 to 100 lb (with maximum velocity limit of 100 mm/s)

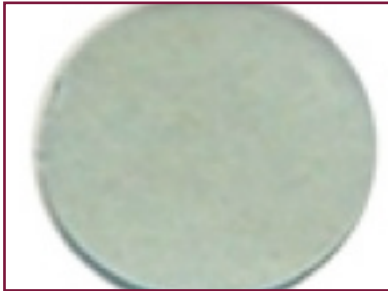
Logging: Critical force, distance, velocity, upper/lower platen vacuum, upper/lower platen temperature, z-position, and entire process duration time

Excess Force Sensing: Failsafe error recovery

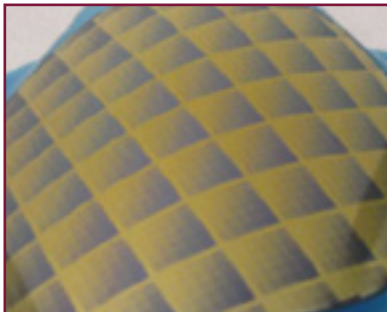
## Successfully qualified with the following device wafer types:



GaAs: diameter: 3 in, 100 mm, 150 mm; thickness: 50-170  $\mu\text{m}$



SiC\*: diameter: 100-150 mm; and InP: diameter: 100 mm; thickness: 50-170  $\mu\text{m}$



Si: diameter: 3 in to 200 mm; thickness: 50-725  $\mu\text{m}$

\*SiC image courtesy of Silicon Quest International, Inc.

## Utility Requirements & Dimensions

Exhaust: 20-30 cfm at 1" W.G. (4" OD exhaust duct)

Electrical: Voltage range 208-240 V, single phase, 50/60 Hz, 3500 W

Power Requirements: 18 amps

Vacuum: -25" to -27" Hg (optimal vacuum: -27" Hg, 4.5 m<sup>3</sup>/h)

Nitrogen or CDA: 100 psi, 1 cfm

Optional Enclosure Purge: 3/8" push-to-connect (PTC tube) (20 psi)

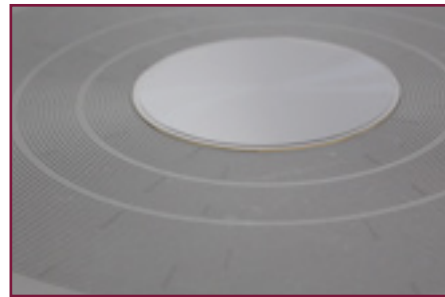
Dimensions: 49" W x 39.5" D x 52.5" H (125 cm W x

100 cm D x 133 cm H)

Machine Weight: 415 lb (187 kg)

Shipping Weight: 1,280 lb

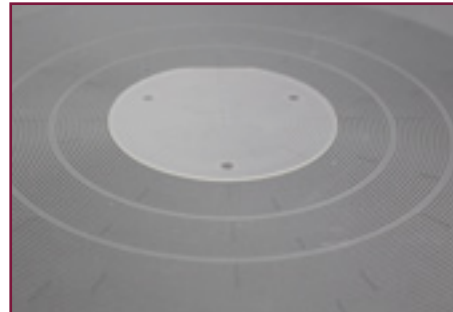
## Compatible bonded-pair carrier materials and sizes:



Sapphire carriers: diameter: 3 in to 150 mm; thickness: 1-1.5 mm



Si carriers: diameter: 2 in to 200 mm; thickness: 280-725  $\mu\text{m}$



Glass carriers: diameter: 2 in to 200 mm; thickness: 280-725  $\mu\text{m}$